EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L14	19	"5418058"	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/10 08:32
L15	21	("4050936" | "5151110" | "5326585" | "5374184" | "5397642" | "5407818" | "5418058" | "5445920" | "5468374" | "5536783" | "5567794" | "5792821" | "5910551" | "5929131" | "6033773" | "6180739" | "6316268" | "6527961").PN. OR ("6670286").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/10 09:33
S1	1	("5900128").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 08:35
S2	13	("4961833" | "5035791" | "5200051" | "5284140" | "5376255" | "5393399" | "5431806" | "5510013" | "5518601").PN. OR ("5900128").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 08:36
S3	2318	(204/424-430). CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/09 09:06
S4	32	S3 and drain and source	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 09:07
S5	152500	(FET or (field effect transistor))	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 09:20
S6	138378	S5 and (counter or reference)	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 09:21
S7	28512	S6 and gas	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 09:21

S8	17321	S7 and drain	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 09:26
S9	17148	S8 and source	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 09:26
S10	215	S9 and ISFET	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 09:28
S11	53	SGFET or (suspend$ gate field electrode transistor)	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 09:34
S12	67	SGFET or (suspend$ gate field electrode transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/09 09:37
S13	4	S12 and hydrophobic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/09 09:58
S14	82	SGFET or (suspend$ gate field electrode transistor) or (suspended gate FET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/09 11:24
S15	2318	(204/424-430). CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/09 12:23
S16	77	S15 and hydrophobic	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 12:23
S17	17	S16 and fluoride	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 12:24
S18	40	S15 and (FET or (field effect transistor))	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 12:26
S19	7	S18 and hydrophobic	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 12:26
S20	3	S19 and fluori$5	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 12:27
S21	152500	(FET or (field effect transistor))	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 12:29
S22	31281	S21 and gas	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 12:29
S23	1791	S22 and hydrophobic	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 12:29

S24	163	S22 and (hydrophobic same fluori$6)	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 12:30
S25	191	S22 and (hydrophobic same fluor$6)	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 13:00
S26	109	S22 and (hydrophobic same fluoro$6)	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 13:00
S27	11070	(contact angle) and hydrophobic	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 13:17
S28	150	fluoro acrylate	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 13:20
S29	1518	fluoroacrylate	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 13:20
S30	1625	S28 or S29	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 13:20
S31	3	S30 and (FET or (field effect transistor))	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/09 13:21
S32	31	3M fluoroacrylate coating "722" contact angle	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/09 13:26

12/10/2008 10:11:04 AM
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